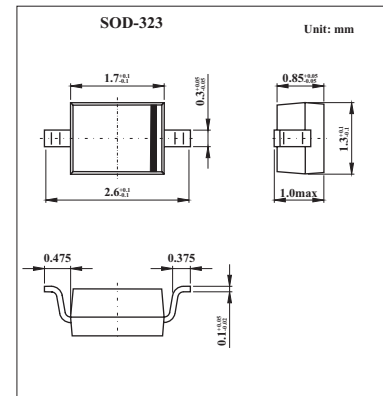


## Silicon Epitaxial Planar Diode

## 1SV322

## ■ Features

- High Capacitance Ratio:  $C_{1V}/C_{4V}=4.3$ (Typ.)
- Low Series Resistance:  $r_s=0.4 \Omega$  (Typ.)
- Useful for Small Size Tuner

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	10	V
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	$V_R$	$I_R = 1 \mu\text{A}$	10			V
Reverse Current	$I_R$	$V_R = 10 \text{V}$			3	nA
Capacitance	$C_{1V}$	$f = 1 \text{MHz}; V_R = 1 \text{V}$	26.5		29.5	pF
	$C_{4V}$	$f = 1 \text{MHz}; V_R = 4 \text{V}$	6		7.1	
Capacitance Ratio	$C_{1V}/C_{4V}$		4	4.3		
Series Resistance	$r_s$	$V_R = 4 \text{V}, f = 470 \text{MHz}$		0.4	0.8	$\Omega$

## Note

1. Signal level when capacitance is measured:  $V_{sig} = 500 \text{mVrms}$

## ■ Marking

Marking	V7
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